

IN THE CLAIMS:

Claims 3, 5, 8 and 10 have been amended herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-2. (Canceled)

3. (Currently amended) A semiconductor device for operable connection to a carrier substrate, the semiconductor device comprising:
a regulator circuit for receiving an electrical power signal;
a semiconductor substrate;
active circuit devices on the semiconductor substrate; and
an on-chip capacitor having at least a portion thereof formed in an active area of the semiconductor substrate, the on-chip capacitor being operably coupled in a shunt configuration to the regulator circuit and operably coupled in a shunt configuration to the active circuit devices to provide filtering capacitance for the semiconductor device.

4. (Original) The semiconductor device of claim 3, wherein the on-chip capacitor comprises a planar-type capacitor.

5. (Currently amended) The semiconductor device of claim 3, wherein the on-chip capacitor includes a first node and a second node, one ~~node~~ of the first and second nodes comprising a poly layer and the other one ~~node~~ of the first and second nodes comprising a channel.

6-7. (Canceled)

8. (Currently amended) A semiconductor device for connection to a carrier substrate configured to provide power and ground thereto, the semiconductor device comprising:
a semiconductor substrate having active circuit elements formed on an active area thereof;
at least one regulator circuit for receiving power; and
at least one capacitor on the semiconductor substrate, at least a portion of the at least one capacitor being formed on the active area, the at least one capacitor being operably coupled in a shunt configuration to the at least one regulator circuit and to the active circuit elements to provide filtering capacitance for the active circuit elements when the semiconductor device is operably connected to power and ground of the carrier substrate

9. (Original) The semiconductor device of claim 8, wherein the at least one capacitor comprises a planar-type capacitor.

10. (Currently amended) The semiconductor device of claim 8, wherein the at least one capacitor includes a first node and a second node, one ~~node~~ of the first and second nodes comprising a poly layer and the other one ~~node~~ of the first and second nodes comprising a channel.